

BAS16TW-Q1

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BAS16TW-Q1

200mW Surface Mount Switching Diode - 100V

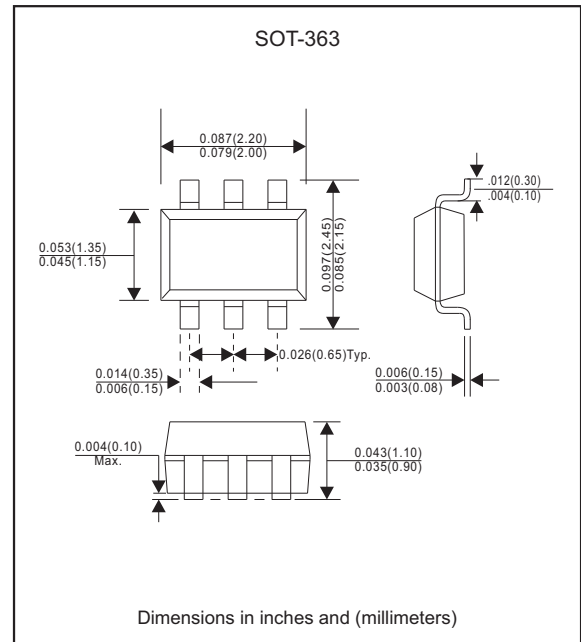
Features

- Fast speed switching.
- For general purpose switching application.
- High conductance.
- Easily connected as full wave bridge
- Silicon epitaxial planar chip.
- Lead-free parts meet RoHS requirements.
- Qualified to AEC-Q101 standards for high reliability.
- Suffix "-H" indicates Halogen-free part, ex. BAS16TW-Q1-H.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-363
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RWM} V_R	75	V
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current (Note 1)	I_{FM}	300	mA
Average Rectified Output Current (Note 1)	I_o	150	mA
Non-Repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	2.0	A
Power Dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}\text{C/W}$
Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Test Condition	Symbol	Min	Max	Unit
Reverse Bread Voltage	$I_R = 10\mu\text{A}$	$V_{(BR)R}$	75		V
Forward Voltage	$I_F = 1.0\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$	V_F		0.715 0.855 1.0 1.25	V
Reverse Current	$V_R = 75\text{V}$ $V_R = 20\text{V}$	I_R		1.0 25	μA nA
Capacitance between terminals	$V_R = 0\text{V}, f = 1\text{MHz}$	C_T		2.0	pF
Reverse recovery time	$I_F = I_R = 10\text{mA}, I_{rr} = 0.1 \times I_R, R_L = 10\Omega$	T_{rr}		4.0	ns

Note:

1. Device mounted on FR-4 PCB, copper pad size 1inch x 0.85inch x 0.062inch

Rating and characteristic curves for each diode(BAS16TW-Q1)

Fig.1 FORWARD CHARACTERISTICS

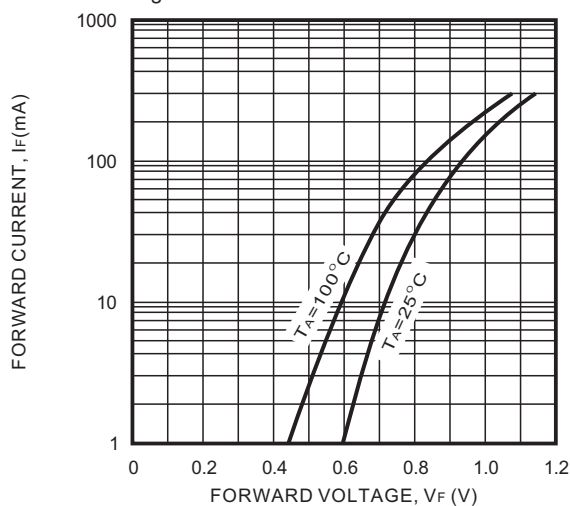


Fig.2 REVERSE CHARACTERISTICS

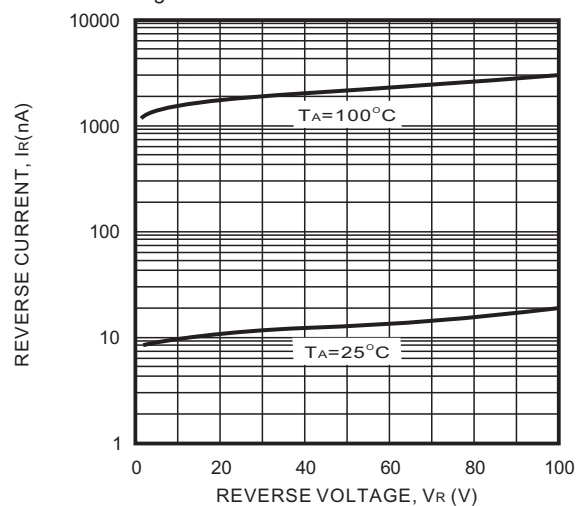


Fig.3 CAPACITANCE CHARACTERISTICS

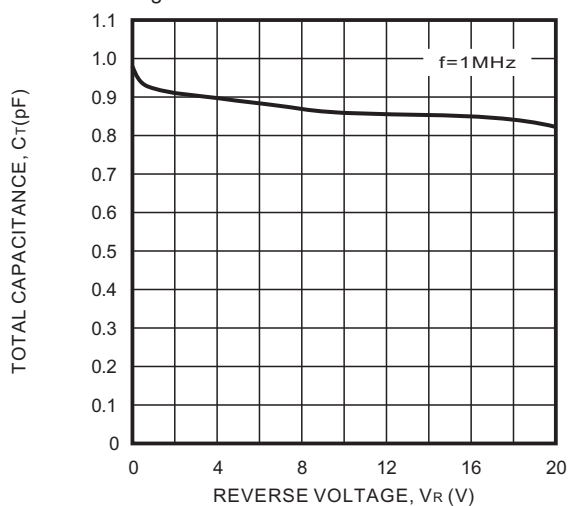
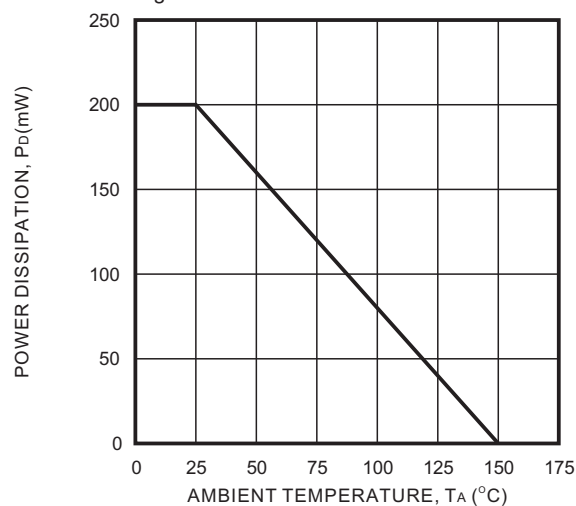
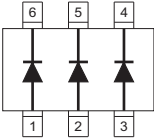


Fig.4 POWER DERATING CURVE



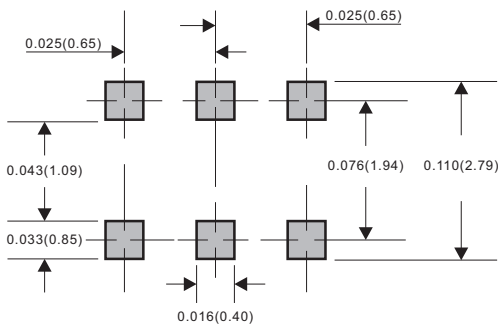
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Pinning information

Type number	Marking Code	Circuit Diagram
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Suggested solder pad layout

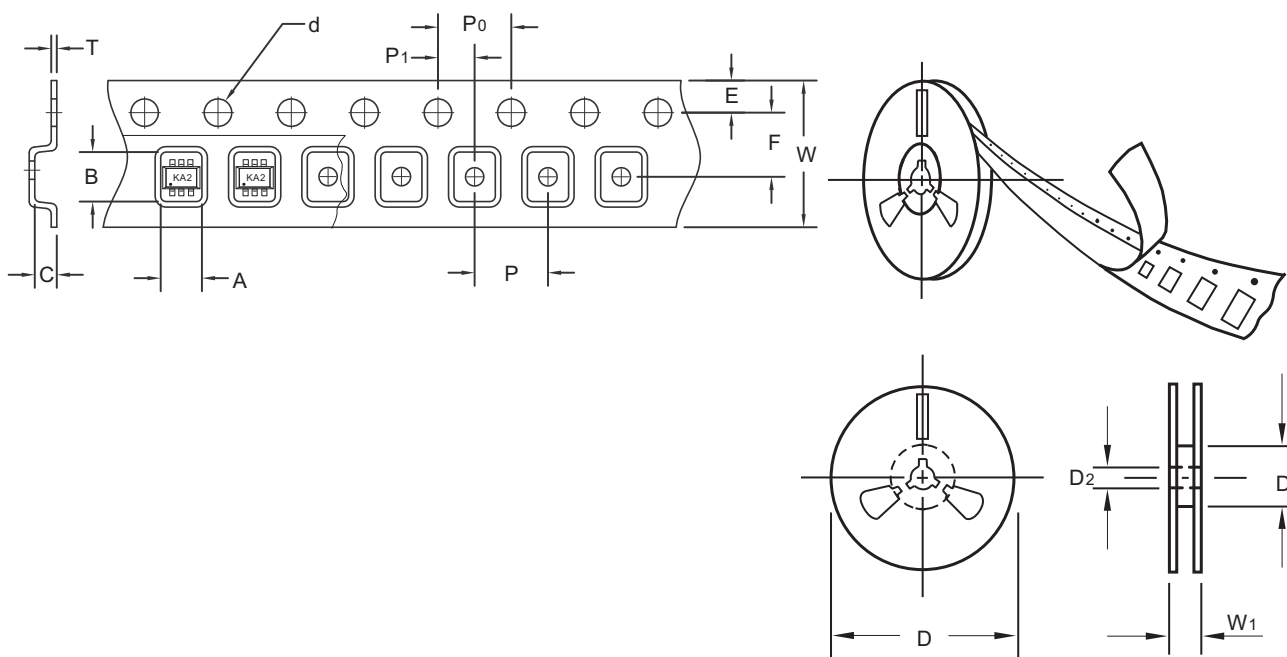
SOT-363



Dimensions in inches and (millimeters)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-363
Carrier width	A	0.1	2.25
Carrier length	B	0.1	2.55
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	12.3

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

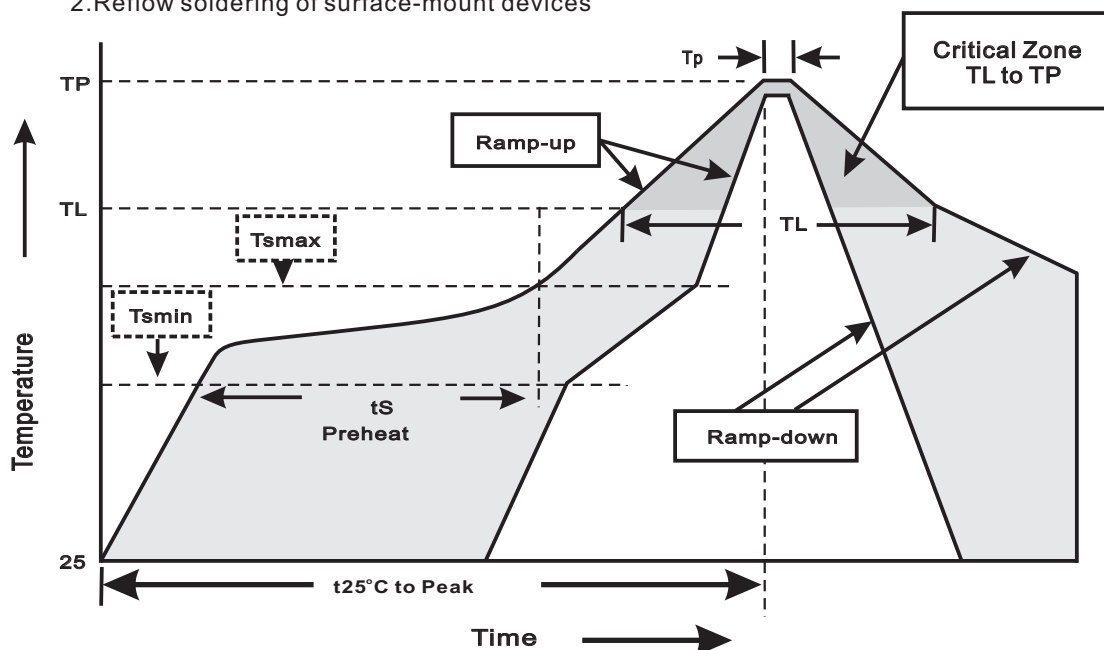
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-363	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	9.50

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smmin}) -Temperature Max(T _{smmax}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smmax} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _p)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%RH+3xIR@260°C+1flux immersion+alcohol+DI H2O rinse	JESD22-A113
2. High Temperature Reverse Bias	$V_{BR}=V_{BR\ Nom}*80\%$ ($T_j=150^{\circ}C$) Test Duration:1000hrs	JESD22-A108
3. High Temperature Storage Life	$T_a=125^{\circ}C$ Test Duration: 1000hrs	JESD22 A-103
4. Temperature Cycle	$-55^{\circ}C$ (15min) to $150^{\circ}C$ (15min) Test Cycles: 1000cycles	JESD22 A-104
5. Autoclave	$P=2atm$ $T_a=121^{\circ}C$ $RH=100\%$ Test Duration:96hrs	JESD22 A-102
6. Solderability	$245\pm5^{\circ}C$ for 5sec	J-STD-002
7. Moisture Resistance	$T_a=85^{\circ}C/85\%$ Relative humidity Test Duration:1000hrs	MIL-STD-750E METHOD 1021.2
8. Resistance To Solder Heat	$260\pm5^{\circ}C$ for 10sec	JESD22 B-106
9. High Temperature High Humidity Reverse Bias	$T_a=85^{\circ}C$, 85%RH, with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration:1000hrs	JESD22-A101